

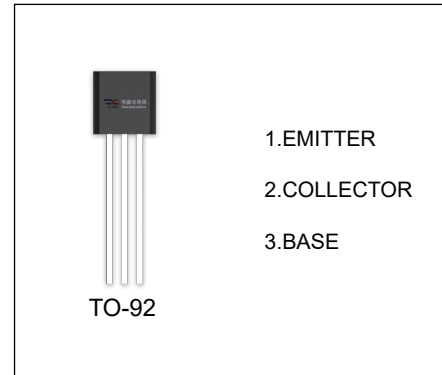
2SC536N TRANSISTOR (NPN)

FEATURES

- Large Current Capacity and Wide ASO.

APPLICATIONS

- Capable of Being Used in The Low Frequency to High Frequency Range.



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC536N	TO-92	Bulk	1000pcs/Bag
2SC536N-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	150	mA
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.01\text{mA}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.01\text{mA}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6\text{V}, I_C=1\text{mA}$	160		560	
	$h_{FE(2)}$	$V_{CE}=6\text{V}, I_C=0.1\text{mA}$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1	V
Collector output capacitance	C_{ob}	$V_{CE}=6\text{V}, f=1\text{MHz}$		3		pF
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=10\text{mA}$		200		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	F	G
RANGE	160-320	280-560